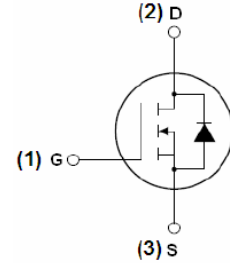


## Trench N-Channel PowerMOSFET Wafer Datasheet

### FEATURES

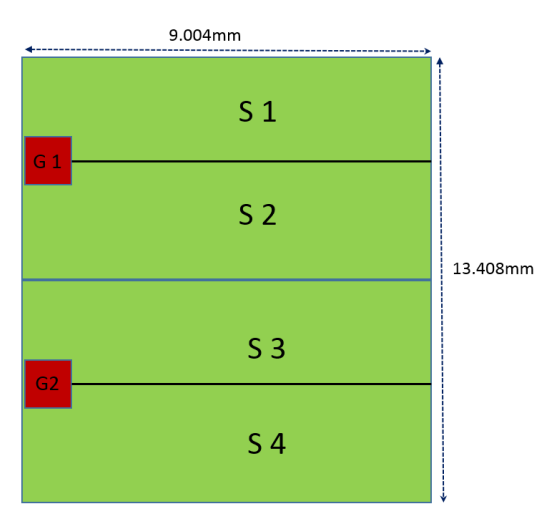
- 100V、500A\* , N-channel
- $R_{DS(on)}=1.6m\Omega(MAX)$
- Ultra low  $Q_{gd}$
- Fast switching



### Electrical Characteristics( $T_J=25^\circ C$ )

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	100			V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-Source On-Resistance		1	1.6	m $\Omega$	$V_{GS}=10V, I_D=250A$
$V_{GS(th)}$	Gate Threshold Voltage	3.0		5.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current			1	$\mu A$	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ C$
$I_{GSS}$	Gate-Body Leakage Current			$\pm 100$	nA	$V_{GS}=\pm 20V$
$V_{SD}$	Body Diode Voltage			1.5	V	$V_{GS}=0V, I_{SD}=500A$
$T_J, T_{stg}$	Operating and Storage Temperature Range	-55~+150			$^\circ C$	

### Mechanical Date

Die Size	13408×9004	$\mu m^2$	
Gate Pad Size	750×1350*2		
Source Pad Size	3000×7500*4		
Scribe Line Size	60	$\mu m$	
Wafer Diameter	200	mm	
Wafer Thickness	175	$\mu m$	
Passivation Frontside	No Passivation	---	
Source Metallization	AlCu , 4.0	$\mu m$	
Drain Metallization	Ti-Ni-Ag 1K-2K-10K	A	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in desiccated nitrogen, with no contamination		

\* Electrical characteristics are reported for the reference packaged part (TO-252/251) and cannot be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.